

10/586810
IAP11 Rec'd PCT/PTO 21 JUL 2006

INFORMATION DISCLOSURE STATEMENT TRANSMITTAL

To Commissioner For Patents

Enclosed herewith is a Form PTO-1449, any required copies of documents listed thereon, and any concise explanation of their relevance is indicated below per 37 CFR 1.97.

<i>Application Number</i>	
<i>Filing Date</i>	
<i>First Named Inventor</i>	MEUNIER-BEILLARD, PHILIPPE
<i>Group Art Unit</i>	
<i>Examiner Name</i>	
<i>Atty. Docket Number</i>	US04 0056 US2

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number No.-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns Lines, Where Relevant Passages or Relevant Figures Appear
	1	US- 5 506 427	04/09/1996	IMAI ET AL.	
	2	US- 5 773 350	06/30/1998	HERBERT ET AL.	
		US-			

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number (ctry ³ -no.-kind ⁴ , if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of cited document	Pages, Columns Lines, Where Relevant Passages or Relevant Figures Appear	T ⁵
	1	JP 02 203533	10/26/1990	TOSHIBA CORP		
	2	JP 02 205033	10/26/1990	HITACHI LTD		

NON-PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in capital letters), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁵
	1	DONKER J. J. T. M. : "VERTICAL PROFILE OPTIMISATION OF A SELF-ALIGNED SiGeC HBT PROCESS WITH AN n-CAP Emitter"; BIPOLE/BICMOS CIRCUIT AND TECHNOLOGY MEETING 2003; PP 111-114.	
	2	P. D. AGNELLO : "GROWTH RATE ENHANCEMENT OF HEAVY n- AND p-TYPE DOPED SILICON DEPOSITED BY ATMOSPHERIC-PRESSURE CHEMICAL VAPOR DEPOSITION AT LOW TEMPERATURE"; JOURNAL ELECTROCHEM SOCIETY VOL. 140 NO. 9; 1993 PP 2703.	

Examiner Signature		Date Considered	
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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the